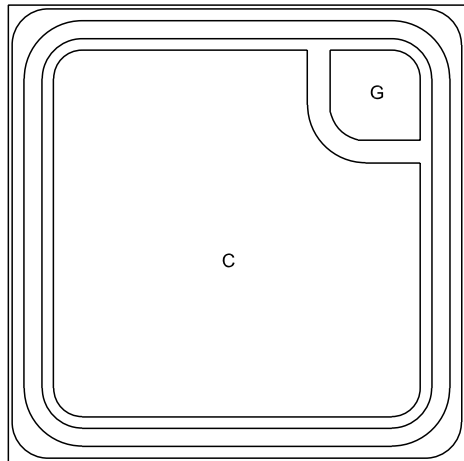


**PROCESS DETAILS**

Process	Glass Passivated Mesa
Die Size	165 x 165 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	131 x 91 MILS
Gate Bonding Pad Area	31 x 31 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

www.DataSheet4U.com

**GEOMETRY**



BACKSIDE ANODE R0

**GROSS DIER PER 4 INCH WAFER**

376

**PRINCIPAL DEVICE TYPES**

CS220-35M Series

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R0 (4- January 2006)